

In the Claims:

1. (Currently Amended) A semiconductor IC (integrated circuit) chip, A semiconductor IC (integrated circuit) chip, A structure for providing a bond area and a probe area on a semiconductor chip, comprising:

a metal line;

an interconnect formed through a dielectric layer connecting to the metal line;

a bond pad on said semiconductor chip having a first portion disposed over the metal line and the interconnect, and a second portion disposed over the dielectric layer and offset from the metal line;

the first portion including a bond area for providing an attachment point for a connection; and

the second portion including a probe area for providing contact with a probe, wherein the bond area is separated from the probe area.

2. (Currently Amended) The semiconductor [[IC]] chip as recited in claim 1, wherein the metal line includes copper.

3. (Currently Amended) The semiconductor [[IC]] chip as recited in claim 1, wherein the bond pad includes aluminum.

4. (Currently Amended) The semiconductor [[IC]] chip as recited in claim 1, further comprising a barrier layer disposed between the interconnect and the metal line to prevent diffusion therebetween.

5. (Currently Amended) The semiconductor [[IC]] chip as recited in claim 1, wherein the bond pad includes a thickness of less than about 2 microns.
6. (Currently Amended) The semiconductor [[IC]] chip as recited in claim 1, further comprising a passivation layer formed on at least a portion of the bond pad to protect the bond pad.
7. (Currently Amended) The semiconductor [[IC]] chip as recited in claim 6, wherein the passivation layer includes a first opening for the bond area and a second opening for the probe area.
8. (Currently Amended) The semiconductor [[IC]] chip as recited in claim 6, wherein the passivation layer includes an opening shared by the bond area and the probe area.
9. (Currently Amended) The semiconductor [[IC]] chip as recited in claim 1, wherein the bond pad is permanently connected to a bond wire.
10. (Currently Amended) A structure for providing a bond area and a probe area on a semiconductor chip semiconductor IC (integrated circuit) chip, comprising:
 - a metal layer patterned to form at least one metal line;
 - a dielectric layer formed on the metal layer and patterned to form a via to the at least one metal line;

a barrier layer formed in contact with the at least one metal line through the via;
an interconnect formed in the via and connecting to the at least one metal line through the barrier layer;
a bond pad on said semiconductor chip having a first portion disposed over the at least one metal line and the interconnect, and a second portion disposed over the dielectric layer and offset from the at least one metal line;
the second portion including [[a]] said probe area on said semiconductor chip for providing contact with a probe for device testing; and
the first portion including [[a]] said bond area on said semiconductor chip for providing an attachment point for a bond wire, wherein the bond area is separate from the probe area.

11. (Currently Amended) The semiconductor [[IC]] chip as recited in claim 10, wherein the metal layer includes copper.

12. (Currently Amended) The semiconductor [[IC]] chip as recited in claim 10, wherein the bond pad includes aluminum.

13. (Currently Amended) The semiconductor [[IC]] chip as recited in claim 10, wherein the barrier layer includes Ta or TaN.

14. (Currently Amended) The semiconductor [[IC]] chip as recited in claim 10, wherein the bond pad includes a thickness of less than about 2 microns.

15. (Currently Amended) The semiconductor [[IC]] chip as recited in claim 10, further comprising a passivation layer formed on the bond pad.
16. (Currently Amended) The semiconductor [[IC]] chip as recited in claim 15, wherein the passivation layer includes a first opening for the bond area and a second opening for the probe area.
17. (Currently Amended) The semiconductor [[IC]] chip as recited in claim 15, wherein the passivation layer includes an opening shared by the bond area and the probe area.
18. (Currently Amended) A structure for providing a bond area and a probe area on a semiconductor chip~~semiconductor IC (integrated circuit) chip~~, comprising:
 - a copper layer patterned to form at least one metal line;
 - a dielectric layer formed on the copper layer and patterned to form a via to the at least one metal line;
 - a diffusion barrier layer formed in contact with the at least one metal line through the via;
 - an aluminum interconnect formed in the via and connecting to the at least one metal line through the diffusion barrier layer, the diffusion barrier layer for preventing atomic mixing between the at least one metal line and the aluminum interconnect;
 - a bond pad on said semiconductor chip integrally formed with the interconnect and having a first portion disposed over the at least one metal line and the interconnect, and a second portion disposed over the dielectric layer and offset from the at least one metal line;

the second portion including [[a]] said probe area on said semiconductor chip for providing contact with a probe for testing the semiconductor IC chip; and

the first portion including [[a]] said bond area on said semiconductor chip for providing an attachment point for a bond wire, wherein the bond area is separate for the probe area.

19. (Currently Amended) The semiconductor [[IC]] chip as recited in claim 18, wherein the barrier layer includes Ta or TaN.

20. (Currently Amended) The semiconductor [[IC]] chip as recited in claim 18, wherein the bond pad includes a thickness of less than about 2 microns.

21. (Currently Amended) The semiconductor [[IC]] chip as recited in claim 18, further comprising a passivation layer formed on the bond pad.

22. (Currently Amended) The semiconductor [[IC]] chip as recited in claim 21, wherein the passivation layer includes a first opening for the bond area and a second opening for the probe area.

23. (Currently Amended) The semiconductor [[IC]] chip as recited in claim 21, wherein the passivation layer includes an opening shared by the bond area and the probe area.